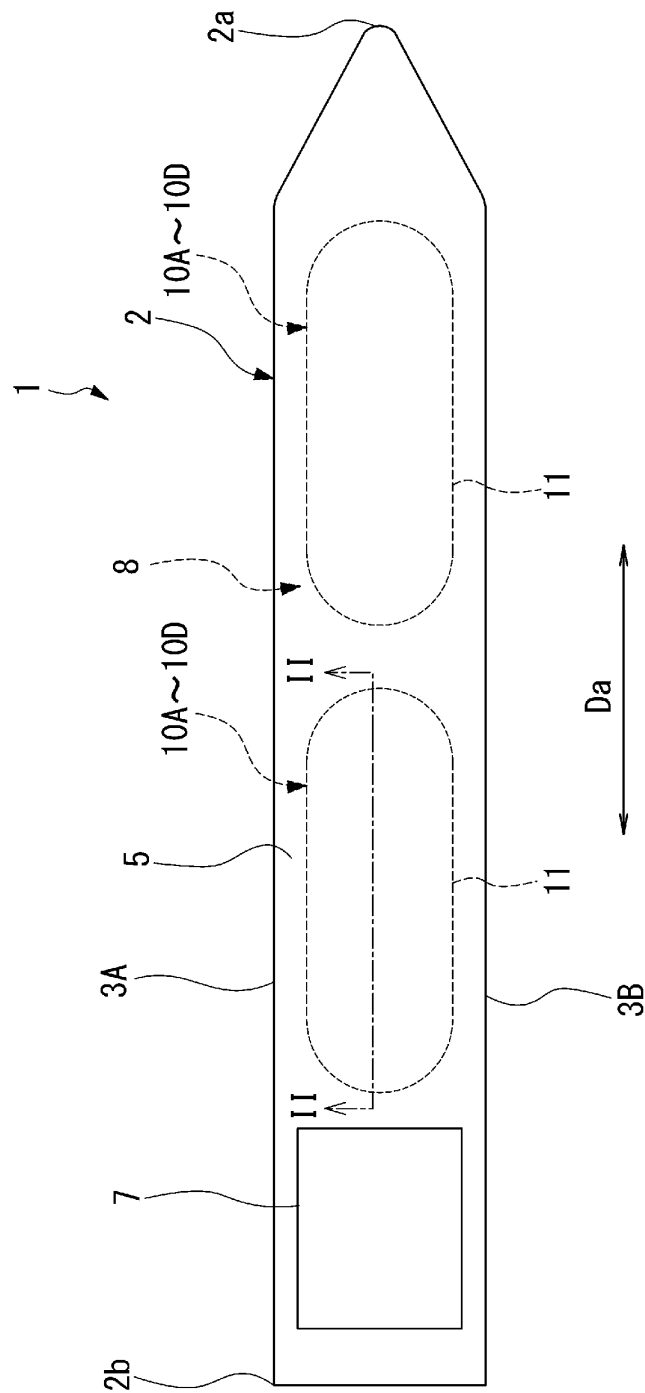
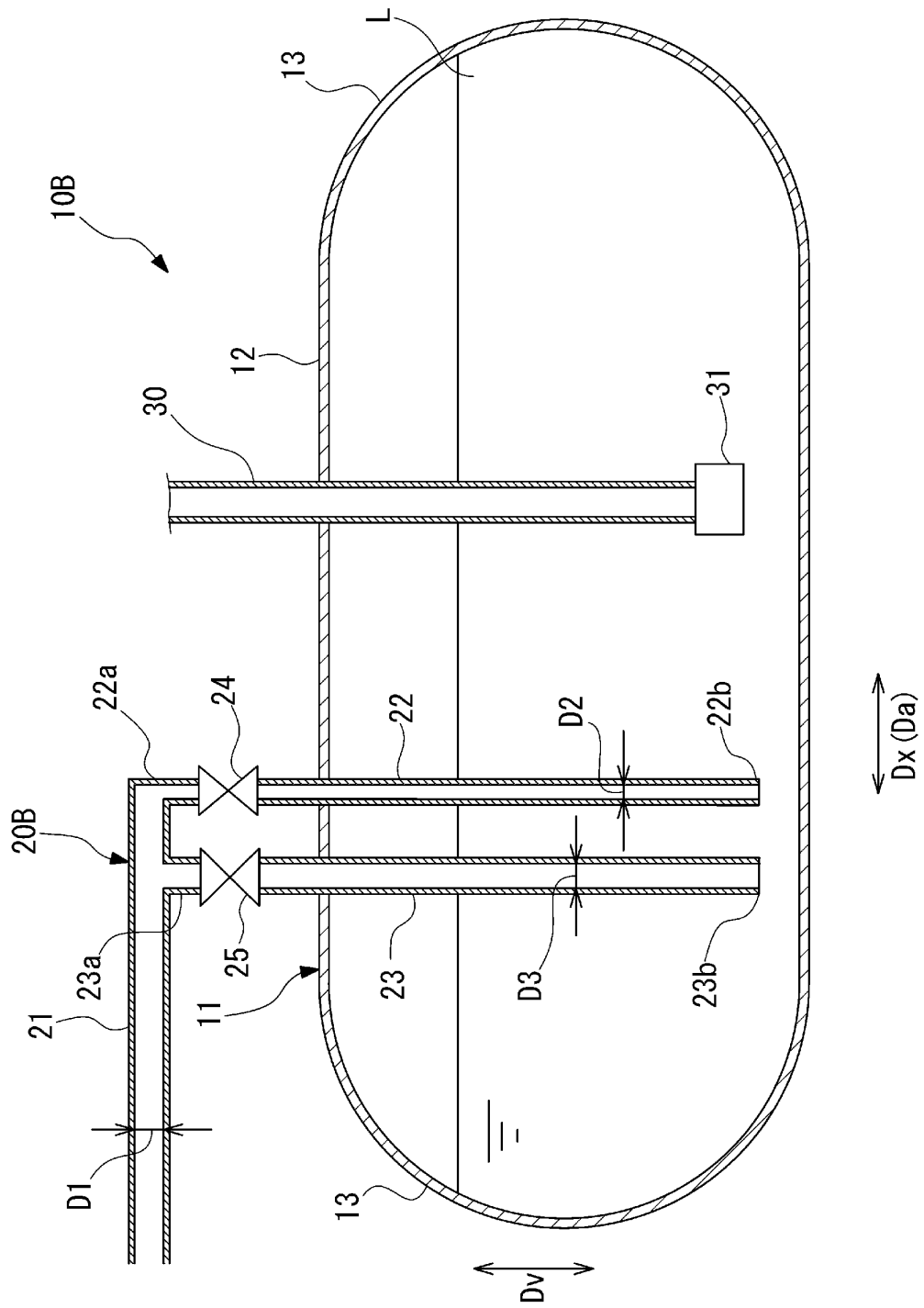


[図1]

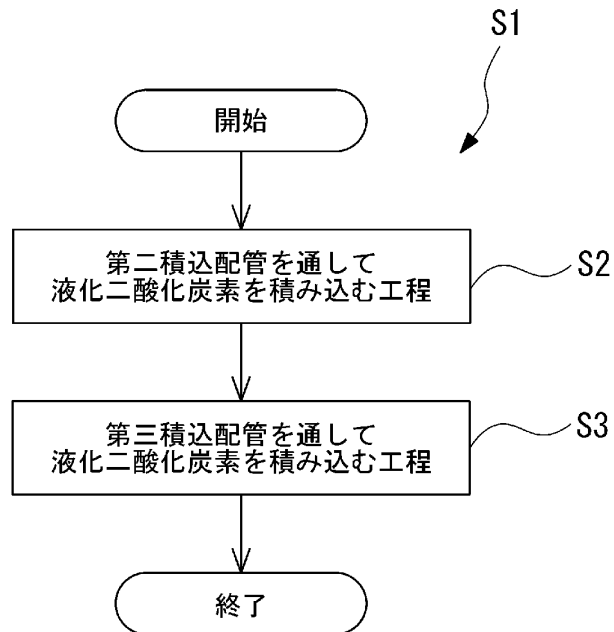




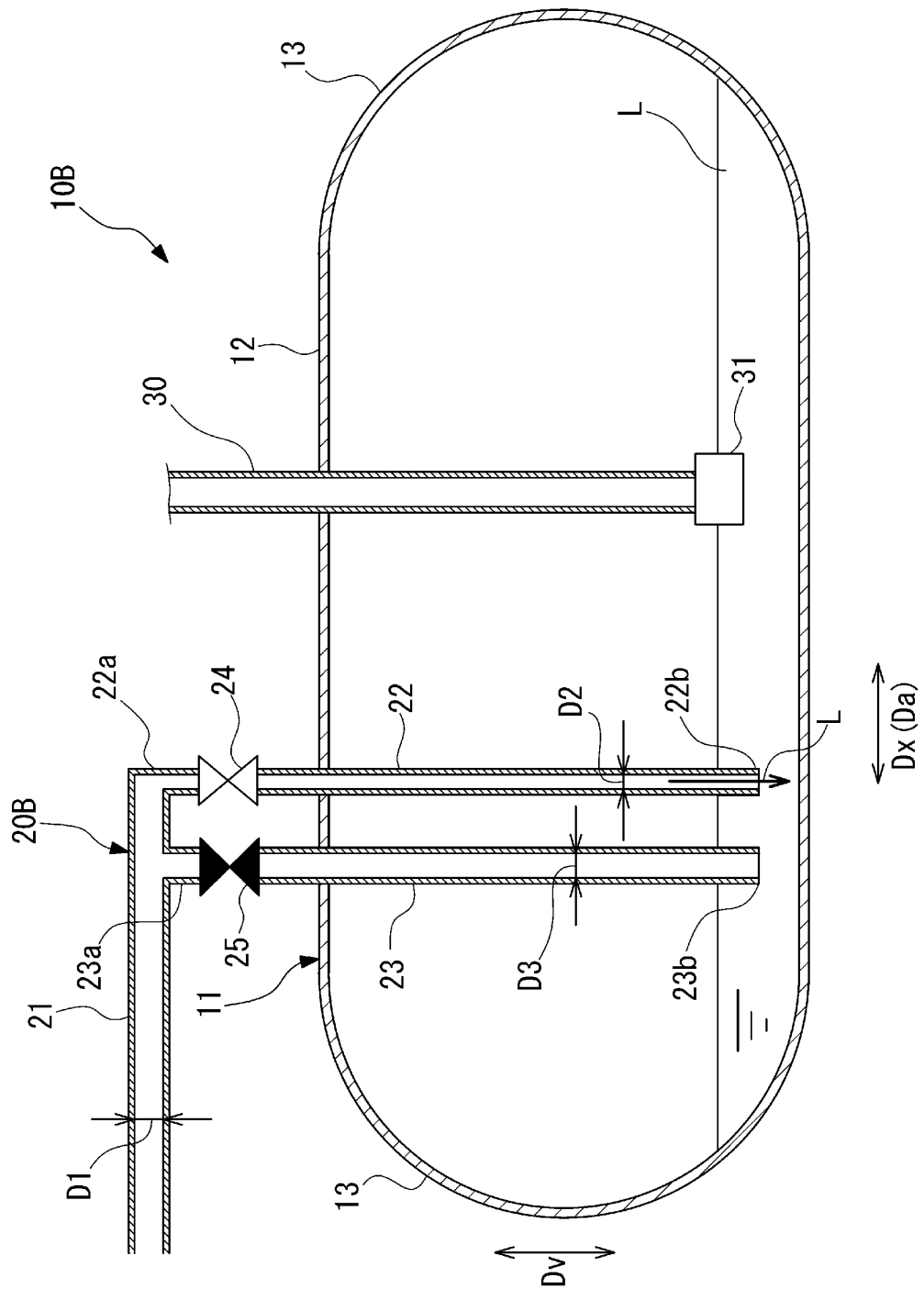
[図3]



[図4]



[図5]

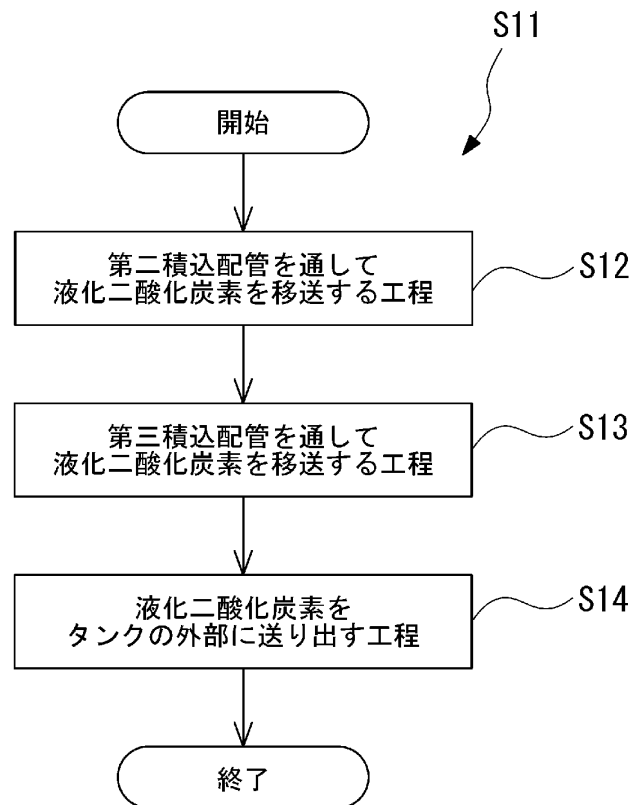




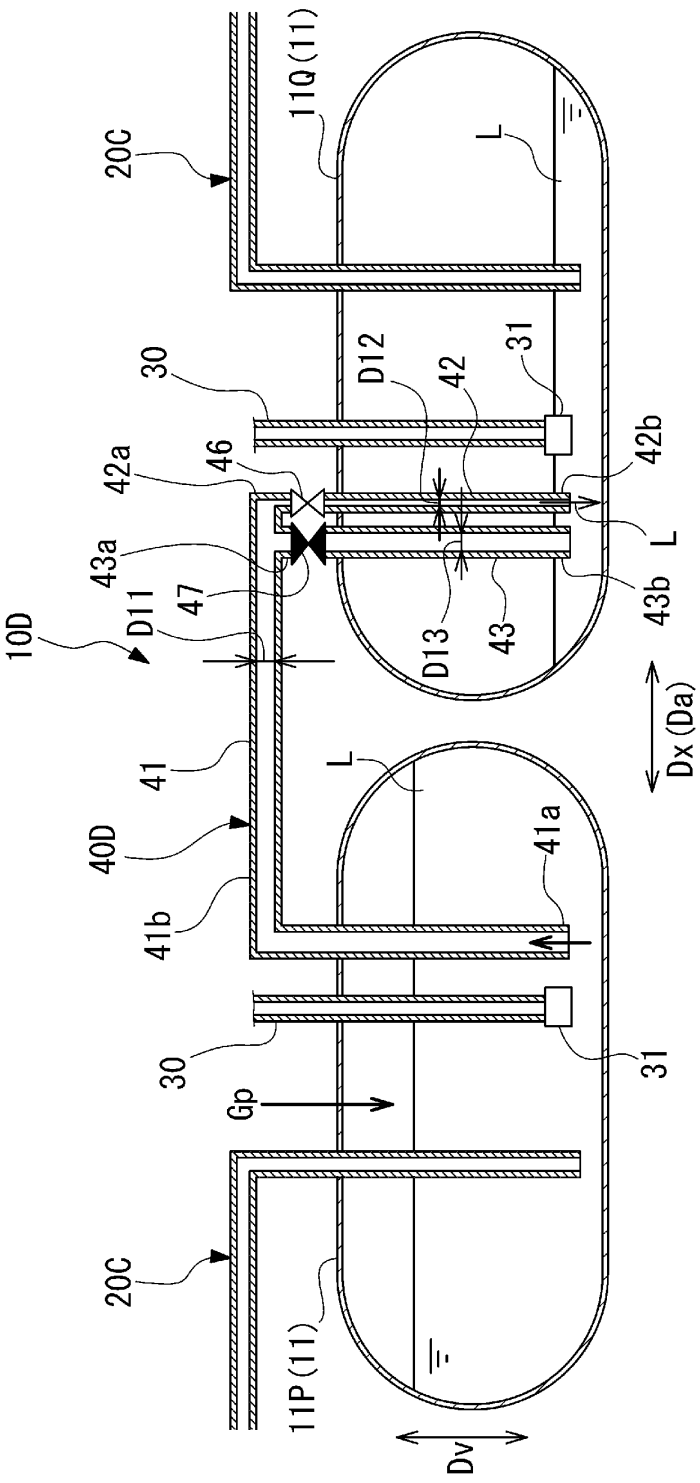




[図9]



[図10]



The diagram illustrates a semiconductor device 10D in a cross-sectional view. A central channel 30 is flanked by two side regions 40D and 42a. The device is built on a substrate 20C. A gate stack 110(11) is positioned over the channel and side regions. Various layers and contacts are labeled with reference numerals: 31, 41, 42, 43, 46, 47, 48, and 49. Dimensions Dv and Dx (Da) are indicated, representing the vertical and horizontal lengths of the device.